11.3-Gbps Limiting Transimpedance Amplifier With RSSI

Check for Samples: ONET8551T

FEATURES

- **9-GHz Bandwidth**
- **10-kΩ Differential Small Signal Transimpedance**
- **–20-dBm Sensitivity**
- **0.9-μA_{RMS} Input Referred Noise**
- **2.5-mA_{p-p} Input Overload Current**
- **Received Signal Strength Indication (RSSI)**
- **92-mW Typical Power Dissipation**
- **CML Data Outputs With On-Chip 50-Ω Back-Termination**
- **On Chip Supply Filter Capacitor**
- **Single +3.3-V Supply**
- **Die Size: 870 µm x 1036 µm**

APPLICATIONS

- **10-G Ethernet**
- **8-G and 10-G Fibre Channel**
- **10-G EPON**
- **SONET OC-192**
- **6-G and 10-G CPRI and OBSAI**
- **PIN and APD Preamplifier-Receivers**

DESCRIPTION

The ONET8551T device is a high-speed, high-gain, limiting transimpedance amplifier used in optical receivers with data rates up to 11.3 Gbps. It features low-input referred noise, 9-GHz bandwidth, 10-kΩ small signal transimpedance, and a received signal strength indicator (RSSI).

The ONET8551T device is available in die form, includes an on-chip VCC bypass capacitor, and is optimized for packaging in a TO can.

The ONET8551T device requires a single +3.3-V supply. The power-efficient design typically dissipates less than 95 mW. The device is characterized for operation from –40°C to 100°C case (IC back-side) temperature.

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

Bond Pad Assignment of ONET8551T (TOP VIEW)

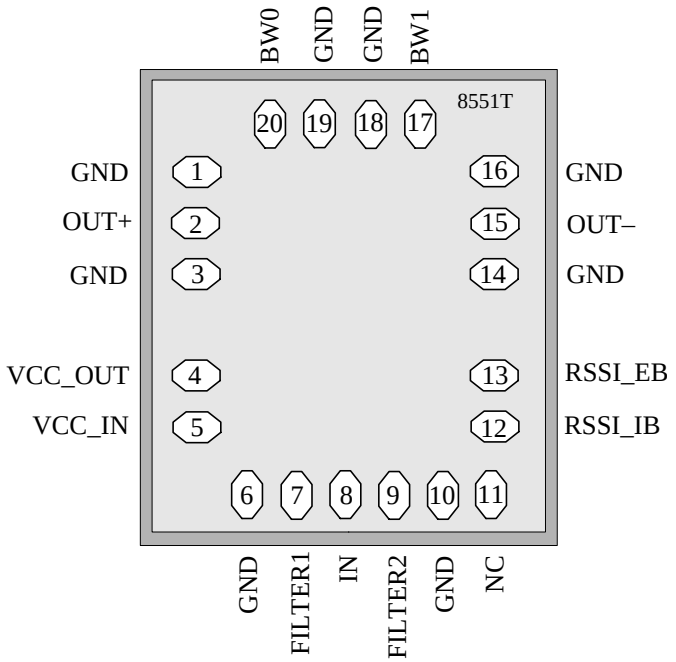

Figure 1. The ONET8551T is available in die form. Bond pad locations are shown in this top view.

Table 1. BOND PAD DESCRIPTION

Pad	Symbol	Type	Description
1, 3, 6, 10, 14, 16, 18, 19	GND	Supply	Circuit ground. All GND pads are connected on die. Bonding all pads is optional. However, for optimum performance, a good ground connection is mandatory.
2	OUT+	Analog output	Non-inverted CML data output; on-chip 50-Ω back-terminated to V_{CC}
4	VCC_OUT	Supply	2.8-V to 3.63-V supply voltage for AGC amplifier
5	VCC_IN	Supply	2.8-V to 3.63-V supply voltage for input TIA stage
7, 9	FILTER	Analog	Bias voltage for photodiode cathode
8	IN	Analog input	Data input to TIA (photodiode anode)
11	NC	No connect	Do not connect
12	RSSI_IB	Analog output	Analog output current is proportional to the input data amplitude. It indicates the strength of the received signal (RSSI), if the photodiode is biased from the TIA. Connected to an external resistor to ground (GND). For proper operation, ensure that the voltage at the RSSI pad does not exceed V_{CC} – 0.65 V. Leave this pad open if the RSSI feature is not used.
13	RSSI_EB	Analog output	Optional use when operated with external PD bias (e.g. APD). Analog output current proportional to the input data amplitude. Indicates the strength of the received signal (RSSI). Connected to an external resistor to ground (GND). For proper operation, ensure that the voltage at the RSSI pad does not exceed V_{CC} – 0.65 V. Leave this pad open if the RSSI feature is not used.
15	OUT–	Analog output	Inverted CML data output; on-chip 50-Ω back-terminated to V_{CC}.
17	BW1	Digital input	Bandwidth adjustment. Ground the pad to increase the bandwidth. Internally pulled-up to V_{CC}
20	BW0	Digital input	Bandwidth adjustment. Ground the pad to increase the bandwidth. Internally pulled-up to V_{CC}
Back-side of die	GND	Supply	Conductive epoxy must be used to attach the die to ground.

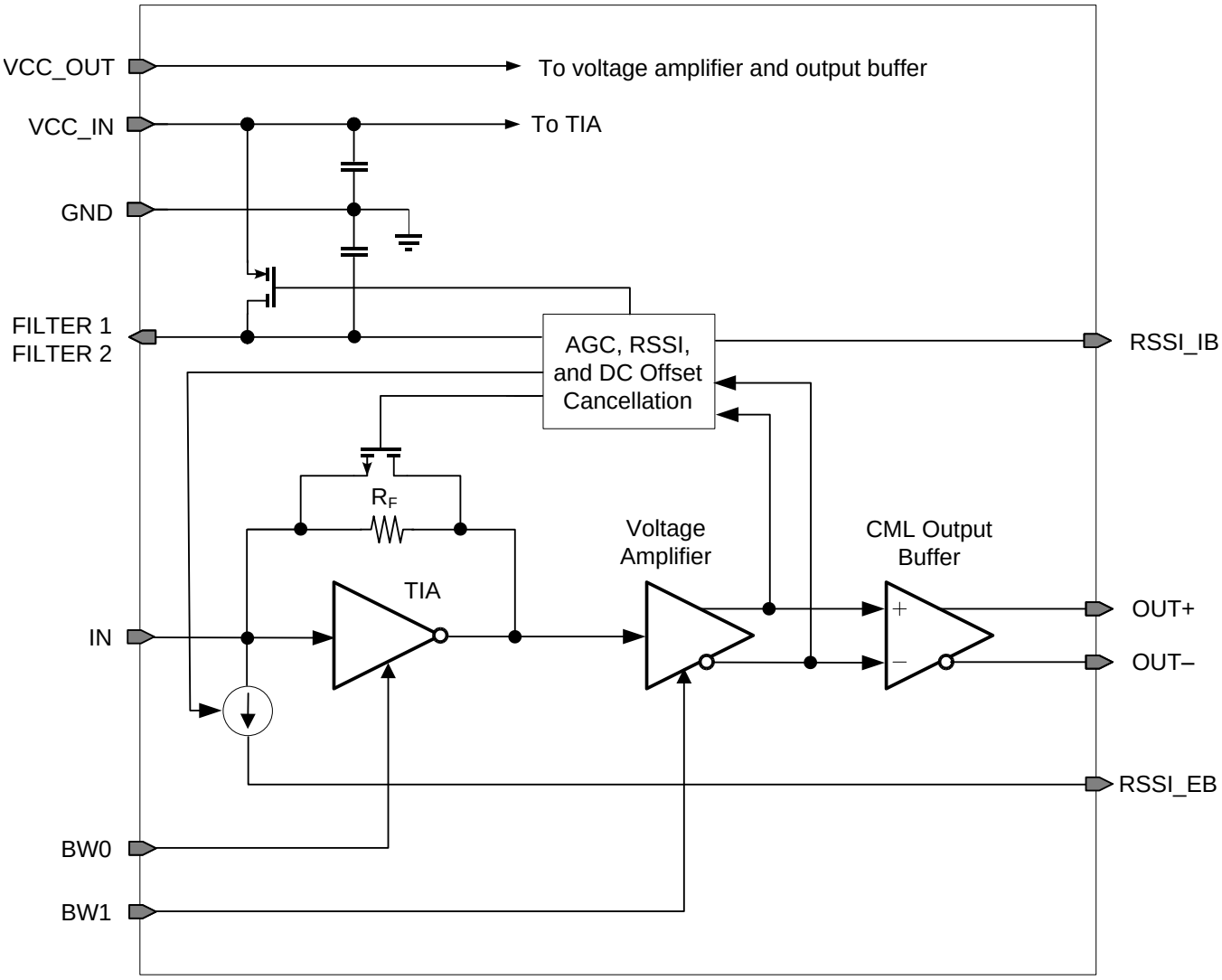

Figure 2. Simplified Block Diagram of the ONET8551T Device

Figure 2 shows a simplified block diagram of the ONET8551T device.

The ONET8551T device consists of the signal path, supply filters, a control block for DC input bias, automatic gain control (AGC), and received signal strength indication (RSSI). The RSSI provides the bias for the TIA stage and the control for the AGC.

The signal path consists of a transimpedance amplifier stage, a voltage amplifier, and a CML output buffer. The on-chip filter circuit provides a filtered VCC for the PIN photodiode and for the transimpedance amplifier.

The DC input bias circuit and automatic gain control use internal low pass filters to cancel the DC current on the input and to adjust the transimpedance amplifier gain. Furthermore, circuitry is provided to monitor the received signal strength.

ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise noted)(1)

		VALUE		UNIT
		MIN	MAX	
V_{CC_IN}, V_{CC_OUT}	Supply voltage(2)	–0.3	4.0	V
V_{BW0}, V_{BW1}, $V_{FILTER1}$, $V_{FILTER2}$, V_{OUT+}, $V_{OUT–}$, V_{RSSI_IB}, V_{RSSI_EB}	Voltage at BW0, BW1, FILTER1, FILTER2, OUT+, OUT–, RSSI_IB, and RSSI_EB(2)	–0.3	4.0	
I_{IN}	Current into IN	–0.7	4.0	mA
I_{FILTER}	Current into FILTER1 and FILTER2	–8	8	
I_{OUT+}, $I_{OUT–}$	Continuous current at outputs	–8	8	
ESD	ESD rating at all pins except input IN	2		kV (HBM)
	ESD rating at input IN	0.5		
T_J	Maximum junction temperature		125	°C

(1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.

RECOMMENDED OPERATING CONDITIONS

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2.80	3.3	3.63	V
T_A	Operating back-side die temperature	–40		100(1)	°C
L_{FILTER}, L_{IN}	Wire-bond inductance at pins $FILTER_i$ and IN		0.3	0.5	nH
C_{PD}	Photodiode capacitance		0.2		pF

(1) 105°C max junction temperature.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions with BW0 = GND and BW1 = Open (unless otherwise noted). Typical values are at V_{CC} = +3.3 V and T_A = 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage		2.80	3.3	3.63	V
I_{VCC}	Supply current	Input current I_{IN} < 1000 μA_{P-P}		28	40 (1)	mA
I_{VCC}	Supply current	Input current I_{IN} < 2500 μA_{P-P}			45 (1)	mA
V_{IN}	Input bias voltage		0.75	0.85	0.98	V
R_{OUT}	Output resistance	Single-ended to V_{CC}	40	50	60	Ω
V_{FILTER}	Photodiode bias voltage (2)		2.55	3.2		V
A_{RSSI_IB}	RSSI gain internal bias	Resistive load to GND (3)	0.49	0.51	0.54	A/A
	RSSI internal bias output offset current (no light)		0	0.9	2.5	µA
A_{RSSI_EB}	RSSI gain external bias	Resistive load to GND (3)	0.46		0.63	A/A
	RSSI external bias output offset current (no light)			25		µA

(1) Including RSSI current
(2) Regulated voltage typically 100 mV lower than V_{CC}.
(3) The RSSI output is a current output, which requires a resistive load to ground (GND). The voltage gain can be adjusted for the intended application by choosing the external resistor. However, for proper operation, ensure that the voltage at RSSI does not exceed V_{CC} – 0.65 V.

AC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions with BW0 = GND and BW1 = Open (unless otherwise noted). Typical values are at V_{CC} = +3.3 V and T_A = 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Z_{21}	Small signal transimpedance	Differential output; Input current i_{IN} = 20 μA_{P-P}	7500	10000		Ω
$f_{HSS,\ 3dB}$	Small signal bandwidth	i_{IN} = 20 μA_{P-P} (1)	7	9		GHz
$f_{L,3dB}$	Low frequency –3-dB bandwidth	16 μA_{P-P} < i_{IN} < 2000 μA_{P-P}		30	150	kHz
$i_{N,IN}$	Input referred RMS noise	10-GHz bandwidth (2)		0.9	1.4	µA
S_{US}	Unstressed sensitivity electrical	10.3125 Gbps, PRBS31 pattern, 1310 nm, extinction ratio > 9 dB, BER 10^{-12}		–20		dBm
DJ	Deterministic jitter	25 μA_{P-P}< i_{IN} < 500 μA_{P-P} (10.3125 Gbps, K28.5 pattern)		6	15	ps_{P-P}
		500 μA_{P-P} < i_{IN} < 2500 μA_{P-P} (10.3125 Gbps, K28.5 pattern)		10	24	
$V_{OUT,\ D,\ MAX}$	Maximum differential output voltage	Input current i_{IN} = 500 μA_{P-P}	180	300	420	mV_{P-P}
PSNR	Power supply noise rejection	F < 10 MHz (3), supply filtering according to SFF8431		–15		dB

(1) The small signal bandwidth is specified over process corners, temperature, and supply voltage variation. The assumed photodiode capacitance is 0.2 pF and the bond-wire inductance is 0.3 nH. The small signal bandwidth strongly depends on environmental parasitics. Careful attention to layout parasitics and external components is necessary to achieve optimal performance.
(2) Input referred RMS noise is (RMS output noise) divided by (gain at 100 MHz).
(3) PSNR is the differential output amplitude divided by the voltage ripple on supply. No input current at IN.

DETAILED DESCRIPTION

SIGNAL PATH

The first stage of the signal path is a transimpedance amplifier, which converts the photodiode current into a voltage. If the input signal current exceeds a certain value, the transimpedance gain is reduced by a nonlinear AGC circuit to limit the signal amplitude.

The second stage is a limiting voltage amplifier that provides additional limiting gain and converts the single-ended input voltage into a differential data signal. The output stage provides CML outputs with an on-chip 50-Ω back-termination to V_{CC}.

FILTER CIRCUITRY

The FILTER pins provide a regulated and filtered VCC for a PIN photodiode bias. The supply voltages for the transimpedance amplifier are filtered by on-chip capacitors, thus an external supply filter capacitor is not necessary. The input stage has a separate VCC supply (VCC_IN), which is not connected on chip to the supply of the limiting and CML stages (VCC_OUT).

AGC AND RSSI

The voltage drop across the regulated FILTER FET is monitored by the bias and RSSI control circuit block in the case where a PIN diode is biased using the FILTER pins.

If the DC input current exceeds a certain level, then it is partially cancelled by a controlled current source. This process keeps the transimpedance amplifier stage within sufficient operating limits for optimum performance.

The automatic gain control circuitry adjusts the voltage gain of the AGC amplifier to ensure limiting behavior of the complete amplifier.

Finally this circuit block senses the current through the FILTER FET and generates a mirrored current that is proportional to the input signal strength. The mirrored current is available at the RSSI_IB output and can be sunk to GND using an external resistor. For proper operation, ensure that the voltage at the RSSI_IB pad does not exceed V_{CC} – 0.65 V.

If an APD or PIN photodiode is used with an external bias, then the RSSI_EB pin can be used. However, for greater accuracy under external photodiode biasing conditions, TI recommends deriving the RSSI from the external bias circuitry.

APPLICATION INFORMATION

Figure 3 shows the ONET8551T device used in a typical fiber optic receiver with the internal photodiode bias. The ONET8551T device converts the electrical current generated by the PIN photodiode into a differential output voltage. The FILTER output provides a low-pass filtered DC bias voltage for the PIN. The photodiode must be connected to the FILTER pad for the bias to function correctly, because the bias circuit senses and uses the voltage drop across the FET.

The RSSI output is used to mirror the photodiode output current and can be connected via a resistor to GND. The voltage gain can be adjusted for the intended application by choosing the external resistor. However, for proper operation of the ONET8551T, ensure that the voltage at RSSI never exceeds V_{CC} – 0.65 V. Leave the RSSI output open, if the RSSI output is not used while operating with internal PD bias.

The OUT+ and OUT– pins are internally terminated by 50-Ω pullup resistors to VCC. The outputs must be AC coupled, for example by using 0.1-µF capacitors, to the succeeding device.

For PIN diode applications, TI recommends grounding the BW0 pin. However, for higher bandwidth, the BW1 pin, or both the BW0 and BW1 pins, can be grounded. To reduce the bandwidth, the BW0 and BW1 pins can be left open.

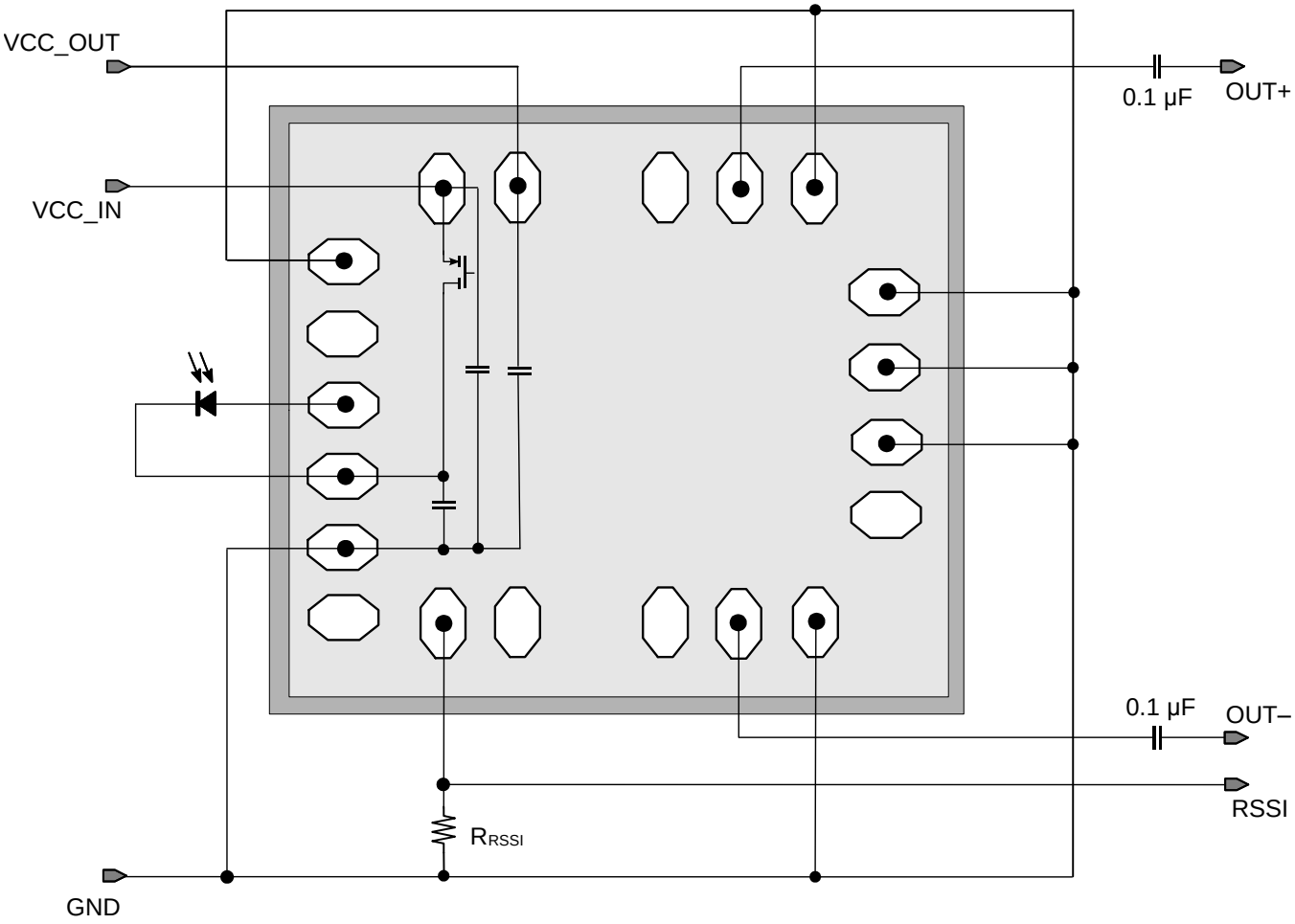

Figure 3. Basic Application Circuit for PIN Receivers

Figure 4 shows the ONET8551T device used in a typical fiber-optic receiver using an external photodiode bias for an avalanche photodiode. To increase the bandwidth using APDs, ground the BW0 and BW1 pins. This configuration can also be used for a PIN diode. However, it may be beneficial to reduce the bandwidth, and therefore the noise, by grounding only the BW0 pin. The external bias RSSI signal is based on the DC offset value and is not as accurate as the internal bias RSSI, which is based on the photodiode current.

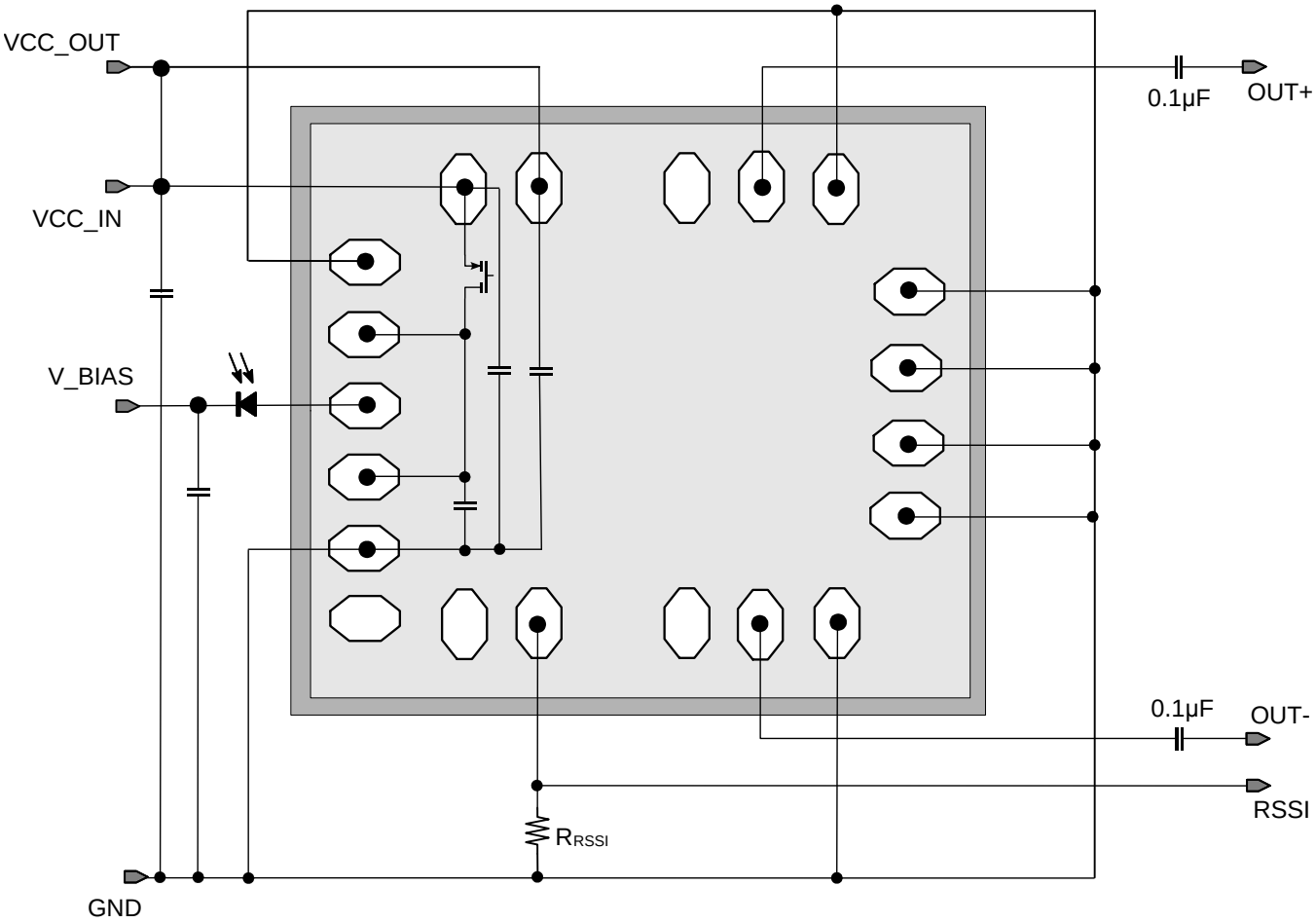

Figure 4. Basic Application Circuit for APD Receivers

DEVICE INFORMATION

ASSEMBLY RECOMMENDATIONS

Careful attention to assembly parasitics and external components is necessary to achieve optimal performance. Recommendations that optimize performance include:

- Minimize the total capacitance on the IN pad by using a low capacitance photodiode and paying attention to stray capacitances. Place the photodiode close to the ONET8551T die in order to minimize the bond wire length, and thus the parasitic inductance.
- Use identical termination and symmetrical transmission lines at the AC coupled differential output pins, OUT+ and OUT–.
- Use short bond wire connections for the supply terminals VCC_IN, VCC_OUT, and GND. Supply voltage filtering is provided on chip, but filtering may be improved by using an additional external capacitor.
- The die has back-side metal. Conductive epoxy must be used to attach the die to ground.

CHIP DIMENSIONS AND PAD LOCATIONS

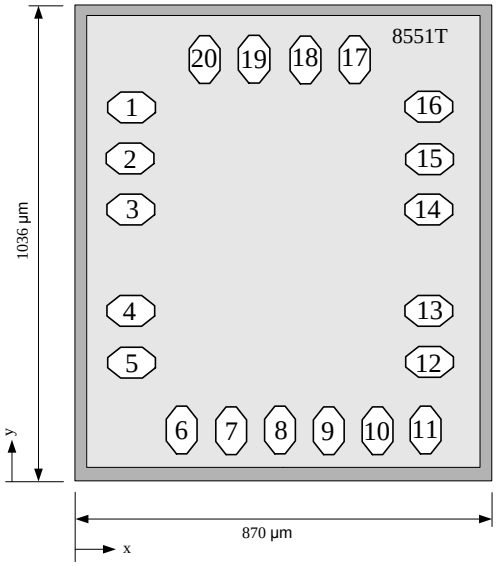

Figure 5. Die Thickness: 203 ±13 µm, Pad Dimensions: 105 µm x 65 µm, and Die Size: 870 ±40 µm x 1036 ±40 µm

PAD	COORDINATES (Referenced to Pad 1)		SYMBOL	TYPE	DESCRIPTION
	x (µm)	y (µm)			
1	0	0	GND	Supply	Circuit ground
2	0	–115	OUT+	Analog output	Non-inverted data output
3	0	–230	GND	Supply	Circuit ground
4	0	–460	VCC_OUT	Supply	3.3-V supply voltage
5	0	–575	VCC_IN	Supply	3.3-V supply voltage
6	116	–728	GND	Supply	Circuit ground
7	226	–728	FILTER1	Analog output	Bias voltage for photodiode
8	336	–728	IN	Analog input	Data input to TIA
9	446	–728	FILTER2	Analog output	Bias voltage for photodiode
10	556	–728	GND	Supply	Circuit ground
11	666	–728	NC	No connect	Do not connect
12	671	–575	RSSI_IB	Analog output	RSSI output signal for internally biased receivers
13	671	–460	RSSI_EB	Analog output	RSSI output signal for externally biased receivers
14	671	–230	GND	Supply	Circuit ground
15	671	–115	OUT–	Analog output	Inverted data output
16	671	0	GND	Supply	Circuit ground
17	508	109	BW1	Digital input	Bandwidth adjustment
18	393	109	GND	Supply	Circuit ground
19	278	109	GND	Supply	Circuit ground
20	163	109	BW0	Digital input	Bandwidth adjustment

TO46 LAYOUT EXAMPLE

Figure 6 shows an example of a layout using a ground-signal-ground (GSG) type PIN photodiode in a 5-pin TO46 can. Figure 7 shows an example of a PIN photodiode with two contacts on the top-side.

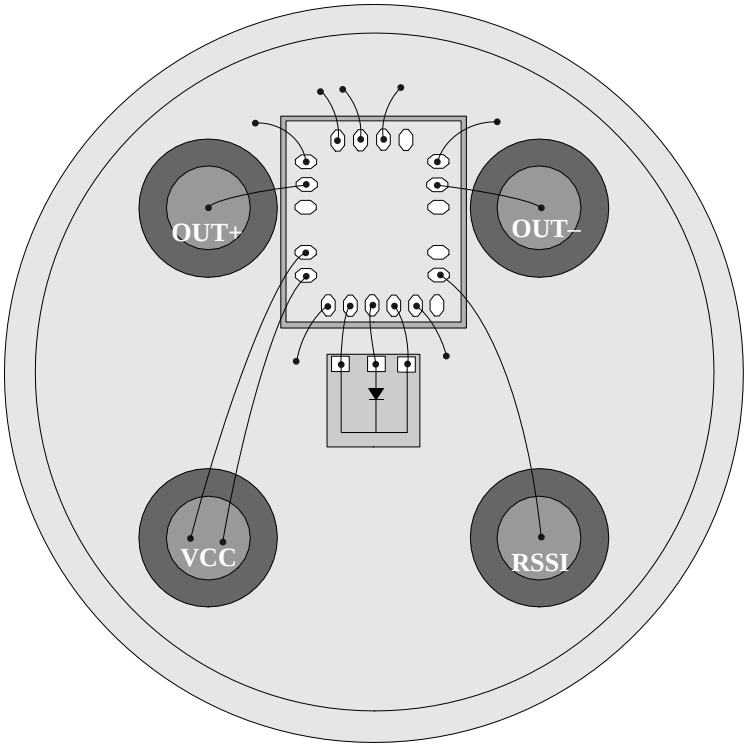

Figure 6. TO46 5-Pin Layout Using the ONET8551T With a GSG PIN Diode

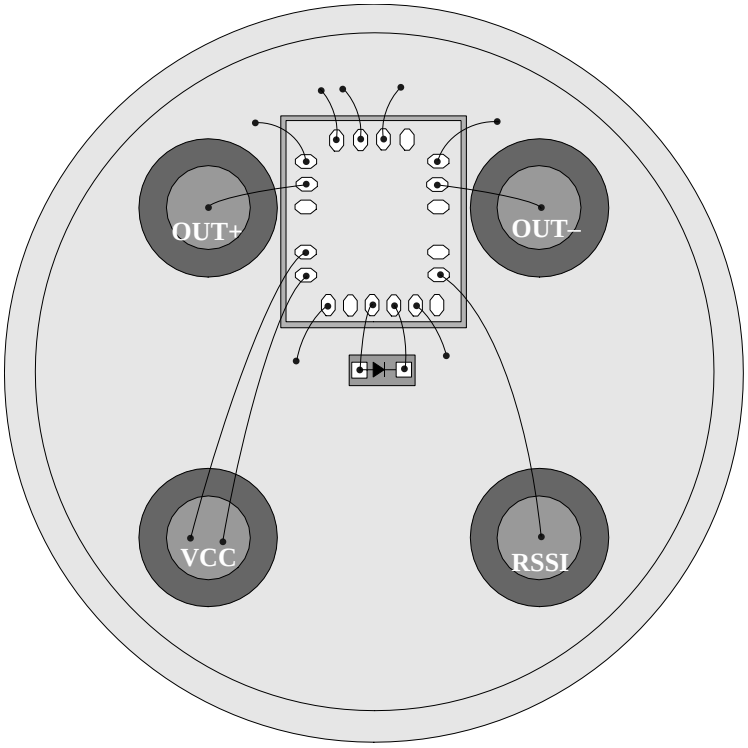

Figure 7. TO46 5-Pin Layout Using the ONET8551T With a Two-Contact PIN Diode

Figure 8 shows an example of a layout using an external bias voltage for the photodiode in a 5-pin TO46 can. Figure 9 shows an example with a back-side cathode contact photodiode using the internal bias voltage.

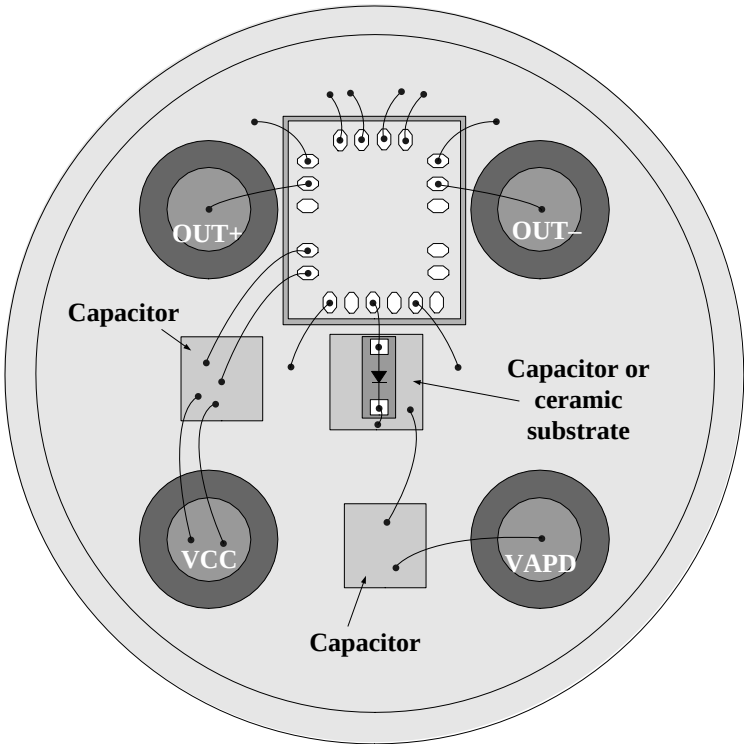

Figure 8. TO46 5-Pin Layout Using the ONET8551T With an Avalanche Photodiode

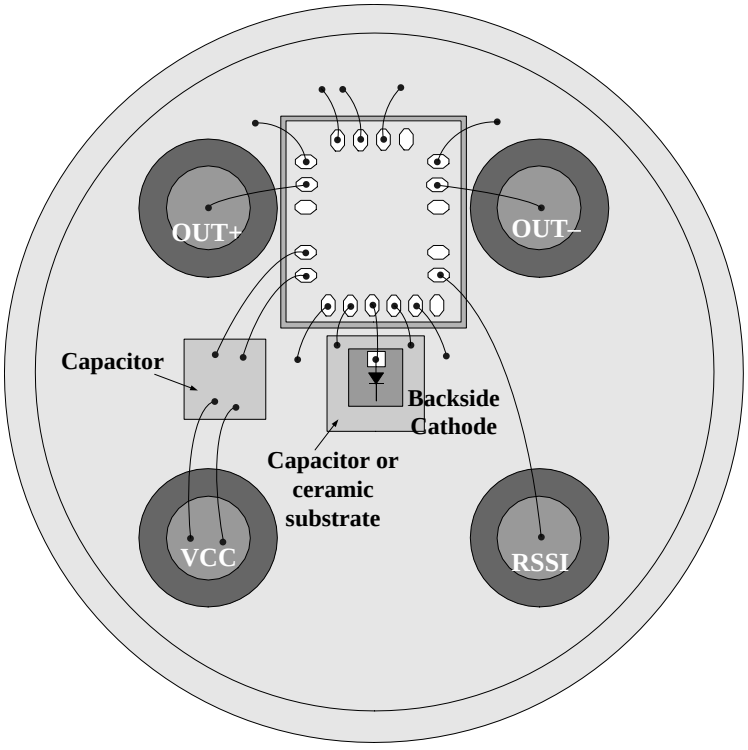

Figure 9. TO46 5-Pin Layout Using the Internal Bias Voltage for a Back-Side Cathode Contact Photodiode

TYPICAL OPERATION CHARACTERISTICS

Typical operating condition is at V_{CC} = +3.3 V and T_A = +25°C (unless otherwise noted).

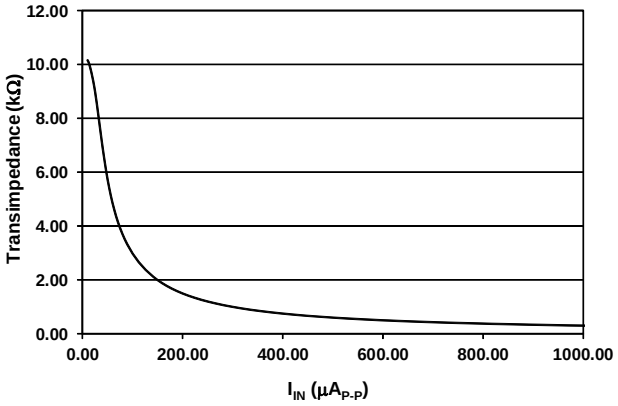

Figure 10.

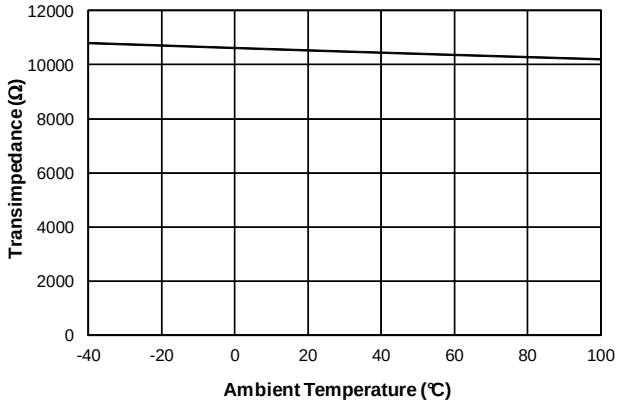

Figure 11.

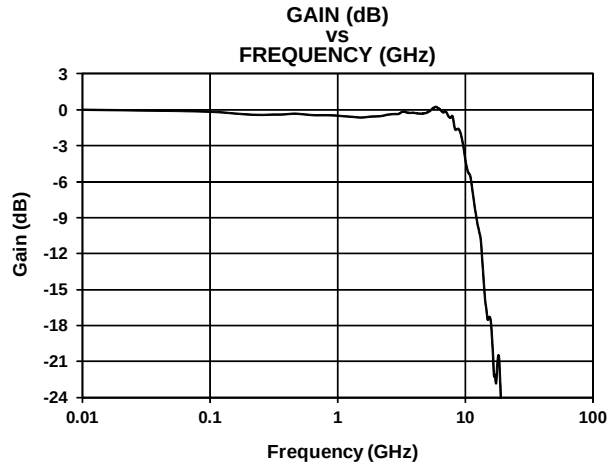

Figure 12. Small Signal Transfer Characteristics

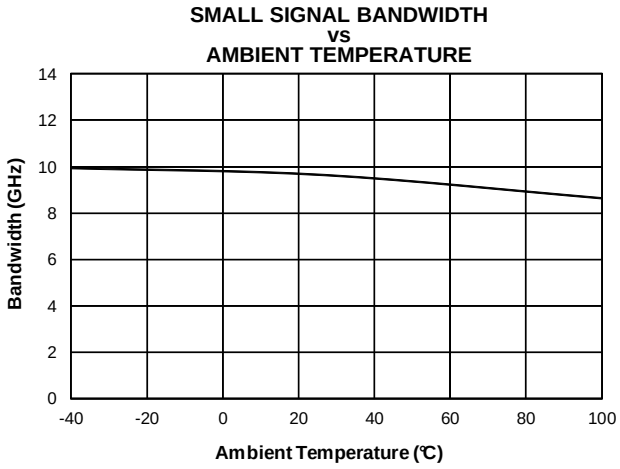

Figure 13.

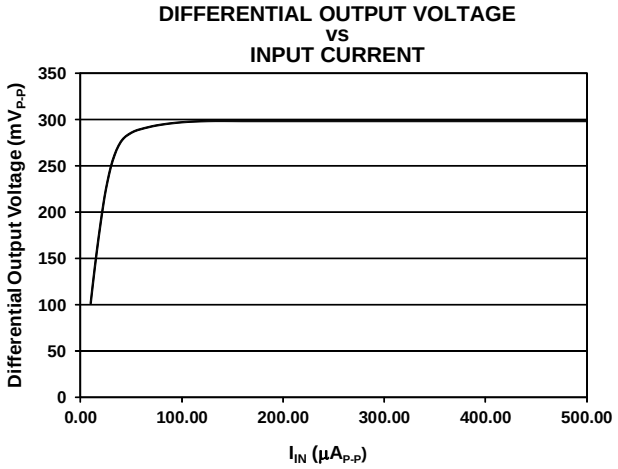

Figure 14.

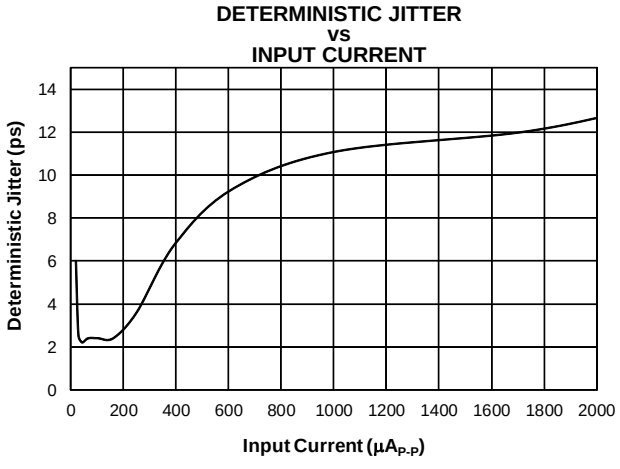

Figure 15.

TYPICAL OPERATION CHARACTERISTICS (continued)

Typical operating condition is at V_{CC} = +3.3 V and T_A = +25°C (unless otherwise noted).

INPUT REFERRED NOISE vs TEMPERATURE

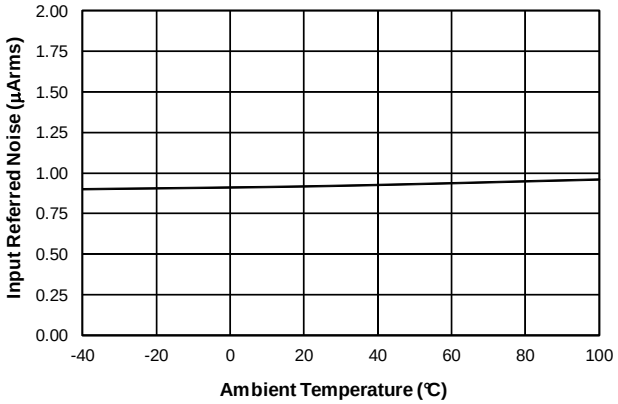

Figure 16.

RSSI_IB OUTPUT CURRENT vs AVERAGE INPUT CURRENT

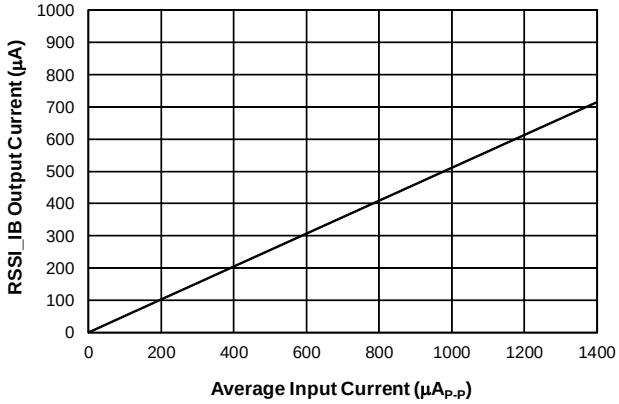

Figure 17.

OUTPUT EYE-DIAGRAM AT 10.3 GBPS AND 20 μA_{P-P} INPUT CURRENT

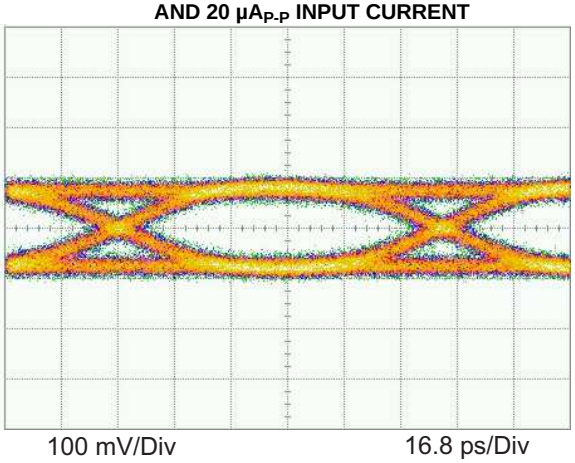

Figure 18.

OUTPUT EYE-DIAGRAM AT 10.3 GBPS AND 100 μA_{P-P} INPUT CURRENT

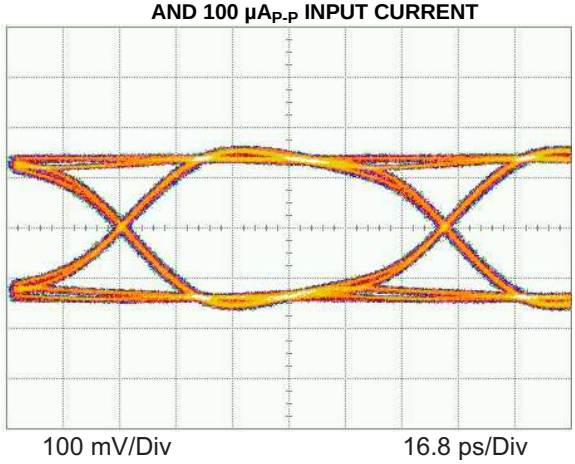

Figure 19.

OUTPUT EYE-DIAGRAM AT 10.3 GBPS AND 500 μA_{P-P} INPUT CURRENT

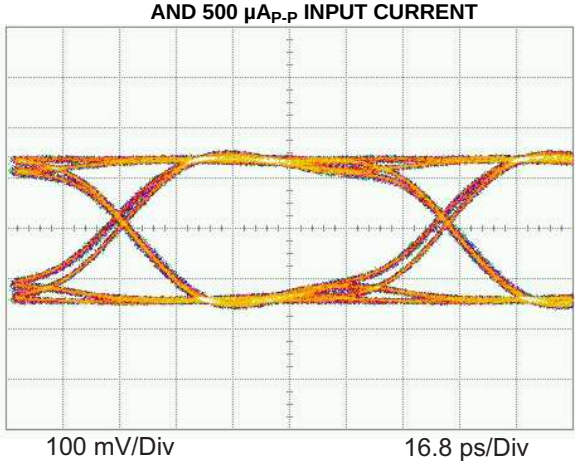

Figure 20.

OUTPUT EYE-DIAGRAM AT 10.3 GBPS AND 2 mA_{P-P} INPUT CURRENT

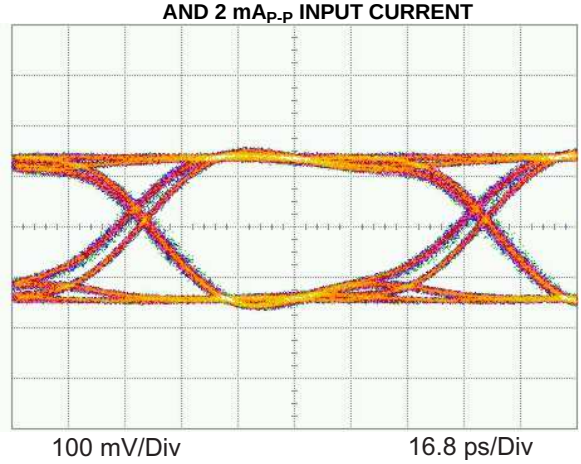

Figure 21.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ONET8551TY	ACTIVE	DIESALE	Y	0	360	Green (RoHS & no Sb/Br)	Call TI	N / A for Pkg Type	-40 to 100		Samples
ONET8551TYS4	ACTIVE	WAFERSALE	YS	0	1	Green (RoHS & no Sb/Br)	Call TI	N / A for Pkg Type	-40 to 100		Samples
ONET8551TYS9	ACTIVE	WAFERSALE	YS	0	1	Green (RoHS & no Sb/Br)	Call TI	N / A for Pkg Type	-40 to 100		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals.
TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as “components”) are sold subject to TI’s terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI’s terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers’ products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers’ products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI’s goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or “enhanced plastic” are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have ***not*** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		**Applications**	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	**TI E2E Community**	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconnectivity		

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265